

# 2N7002W

# **Power MOSFET**

# 300mA, 60V N-CHANNEL **POWER MOSFET**

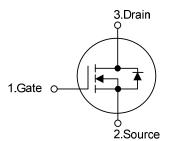
## DESCRIPTION

The UTC 2N7002W uses advanced technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

## **FEATURES**

- \* High Density Cell Design for Low R<sub>DS(ON)</sub>.
- \* Voltage Controlled Small Signal Switch
- \* Rugged and Reliable
- \* High Saturation Current Capability

## **SYMBOL**

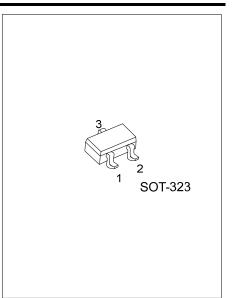


## ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing	
Lead Free	Halogen Free	Fackage	1	2	3	Facking	
2N7002WL-AL3-R	2N7002WG-AL3-R	SOT-323	G	S	D	Tape Reel	
Note: Pin Assignment: G: G							
2N7002WG-AL3-R (1)Packing Type (2)Package Type (3)Green Package		<ul> <li>(1) R: Tape Reel</li> <li>(2) AL3: SOT-323</li> <li>(3) G: Halogen Free and Lead Free, L: Lead Free</li> </ul>					

## MARKING





### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V <sub>DSS</sub>	oss 60		
Drain-Gate Voltage (R <sub>GS</sub> ≤1MΩ)		V <sub>DGR</sub>	60	V	
Gate Source Voltage	Continuous	V <sub>GSS</sub>	±20	V	
	Non Repetitive(t <sub>P</sub> <50µs)	VGSS	±40	v	
Drain Current	Continuous	1-	300	mA	
	Pulsed	ID	800	IIIA	
Power Dissipation		<b>D</b> -	200	mW	
Derated Above 25°C		P <sub>D</sub> -	1.6	mW/°C	
Junction Temperature		TJ	+ 150	°C	
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ <sub>JA</sub>	625 (Note1)	°C/W

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						_
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =10µA	60			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Cata Source Lookage Current	I <sub>GSSF</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V			100	nA
Gate-Source Leakage Current	I <sub>GSSR</sub>	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100	nA
ON CHARACTERISTICS (Note2)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1	2.1	2.5	V
Drain-Source On-Voltage	V <sub>DS (ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =300mA		0.6	3.75	V
Drain-Source On-Voltage		V <sub>GS</sub> = 5.0V, I <sub>D</sub> =50mA	0.09		1.5	v
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =300mA ,T <sub>J</sub> =125°C			13.5	Ω
	NDS (ON)	V <sub>GS</sub> =5.0V, I <sub>D</sub> =50mA			7.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	CISS	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f=1.0MHz		20	50	pF
Output Capacitance	Coss			11	25	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			4	5	pF
Turn-On Time	t <sub>on</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =150Ω, I <sub>D</sub> =200mA,			20	nS
	UN	$V_{GS}$ =10V, $R_{GEN}$ =25 $\Omega$			20	110
Turn-Off Time	t <sub>OFF</sub>	$V_{DD}$ =30V, R <sub>L</sub> =25 $\Omega$ , I <sub>D</sub> =200mA,			20	nS
		V <sub>GS</sub> =10V, R <sub>GEN</sub> =25Ω			20	110
DRAIN-SOURCE DIODE CHARACTE	RISTICS AN	ND MAXIMUM RATINGS	1	1	1	
Maximum Continuous Drain-Source	ls				300	mA
Diode Forward Current						
Maximum Pulsed Drain-Source Diode	I <sub>SM</sub>		2		0.8	А
Forward Current	_	$\sim$	01			
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, Is=300mA (Note)	00,	0.88	1.5	V
Notes: 1. Device mounted on FR-4 PC	B, 1 inch x 0	).85 inch x 0.062 inch. Minimum land	pad siz	e.		
<ol><li>Pulse Test: Pulse Width≤300</li></ol>	µs, Duty Cy	cle ≤ 2.0%.				
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## ■ TEST CIRCUIT AND WAVEFORM

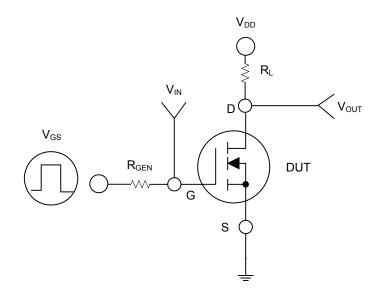
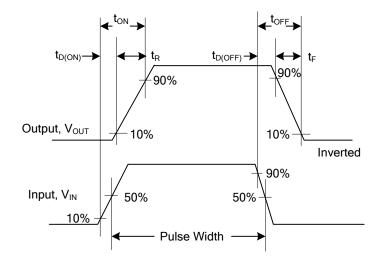


Fig. 1





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